NSN 5961-01-514-2180

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No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-514-2180 **Inclosure Material:** Metal **Overall Length:** 0.975 inches **Overall Height:** 0.200 inches **Overall Width:** 0.670 inches **Mounting Facility Quantity: Mounting Method:** Slot **Features Provided:** Low noise **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 70.0 drain to gate voltage and 70.0 drain to source voltage and 30.0 gate to source voltage **Current Rating Per Characteristic:** 4.00 amperes source cutoff current of standard range **Power Rating Per Characteristic:** 100.0 watts small-signal input power, common-collector absolute **Product Name:** Silicon rf power, vdmos transistor **Special Features:** 8gold metalized; package style - ak; high efficiency; linear; high gain; junction temperature plus 200.0 degrees c; storage temperature minus 65.0 to plus 150.0 degrees c; designed specifically for broadband radio frequency (rf) applications **Terminal Type And Quantity:** 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:**